

NE Please replace the paragraph beginning on page 19, line 14, with the following rewritten paragraph:

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--To achieve the first object, in the semiconductor device, a conductive layer pattern is formed on a substrate and a inter-layer insulating film covering this conductive layer pattern is formed on the substrate. A first connection hole is formed in an upper layer of the inter-layer insulating film above the conductive layer pattern. Further, in this inter-layer insulating film, a second connection hole which reached the conductive layer pattern from the bottom portion of the first connection hole and has a smaller diameter than that of the first connection hole is formed. Further, a conductive plug is formed with the interior of the first connection hole and the second connection hole filled.-

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Please replace the paragraph beginning on page 11, line 6, with the following rewritten paragraph:

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--In the semiconductor device, the diameter of the connection hole formed in the upper portion is made larger than the second connection hole, and the conductive plug is formed in the first and second connection holes so as to fill them. Therefore, the diameter of the upper portion of this plug becomes larger then the diameter of the second connection hole.--

--In the method of manufacturing of the semiconductor device, after the first connection hole is formed in the upper layer of the inter-layer insulating film above the conductive layer pattern, the side wall is formed on the side wall of this first connection hole, and further the second connection hole is formed in the inter-layer insulating film by self-alignment in a state where it is communicated with the conductive layer pattern from the bottom portion of the first connection hole and where the diameter is smaller than that of the first connection hole by utilizing the side wall as a mask. Therefore, the second connection hole having a smaller diameter than that of the first connection hole is formed by only one masking step. The conductive plug is filled in the first connection hole and the second connection hole. Therefore, the diameter of the upper portion of the plug becomes larger than the diameter of the second connection hole.--

Please replace the paragraph beginning on page 16, line 22, with the following rewritten paragraph:

--Fig. 35 to Fig, 56 are sectional views explaining a first step for manufacturing a COB type DRAM according to a third embodiment of the present invention.--

Please replace the paragraph beginning on page 19, line 13, with the following rewritten paragraph:

--In the semiconductor device, the diameter of the first connection hole 216 formed at the upper portion is formed larger than that of the second connection hole 217, then the conductive plug 218 is formed in the first and second connection holes 216

96 and 217 in a state filling them. Therefore, the diameter of the upper portion of this plug 218 becomes larger than the diameter of the part of the plug 218 filled in the second connection hole 217.--

Please replace the paragraph beginning on page 20, line 12, with the following rewritten paragraph:

97 --Further, in the configuration wherein the conductive plug 218 is formed in a state filling the first and second connection holes 216 and 217 and the upper surface of this plug 218 is formed to almost the same height as the surface of the first inter-layer insulating film 215 where the film is formed on the surface of the first inter-layer insulating film 215, the coverage of the film becomes good and, at the same time, no step difference is formed in the lithography step after this, therefore the patterning precision is enhanced.--

Please replace the paragraph beginning on page 22, line 21, with the following rewritten paragraph:

99 --Then, as shown in Fig. 21, a side wall forming film 232 is formed on the inner wall of the first connection hole 216 and the first film 231. This side wall forming film 232 is formed, for example, a doped polysilicone. Subsequently, the part of the side wall forming film 232 indicated by a two dotted chain line is etched back to form the side wall 233 on the side wall of the first connection hole 216 by the side wall forming film 232.--

Please replace the paragraph beginning on page 25, line 16, with the following rewritten paragraph:

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--Next, as shown in Fig. 26, a side wall forming film 243 is formed on the inner wall of the aperture 242 and the third film 241. This side wall forming film 243 is formed buy, for example, a doped polysilicon. Subsequently, by etch back the part of the side wall forming film 243 indicated by the two dotted chain line, a side wall 244 is formed on the side wall of the aperture 242 by this side wall forming film 242.--

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Please replace the paragraph beginning on page 26, line 24, with the following rewritten paragraph:

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--In the method of manufacture of the semiconductor device, the first connection hole 216 is formed in the upper layer of the first inter-layer insulating film 215 above the conductive layer pattern 214a, and further the second connection hole 217 is formed in the first inter-layer insulating film 215 in a state where it is communicated with the conductive layer pattern 214a from the bottom portion of the first connection hole 216 and has a smaller diameter than that of the first connection hole 216. Therefore, the first connection hole 216 formed in the upper portion is formed to have a larger diameter than that of the second connection hole 217. Then since the conductive plug 218 is

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Please replace the paragraph beginning on page 28, line 3, with the following rewritten paragraph:

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